

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1 - 6. (Canceled)

7. (Previously Presented) A method of producing an SOI wafer comprising at least the steps of forming an insulator film on at least one of a bond wafer made of silicon single crystal to form an SOI layer and a base wafer made of silicon single crystal to be a support substrate, bonding each main surface of the bond wafer and the base wafer via the insulator film, and making the bond wafer bonded to the base wafer thinner, wherein the base wafer is one silicon wafer selected from a group consisting of an epitaxial wafer, a nitrogen doped wafer, a hydrogen annealed wafer, a nitrogen doped and annealed wafer, and an entire N-region wafer.

8. (Currently Amended) A method of producing an SOI wafer comprising at least the steps of forming an insulator film on at least one of a bond wafer made of silicon single crystal to form an SOI layer and a base wafer made of silicon single crystal to be a support substrate, forming a micro bubble layer in the bond wafer by implanting gas ions from a main surface of the bond wafer, bonding the ion-implanted main surface of the bond ~~wafer~~ wafer to a main surface of the base wafer via the insulator film, and delaminating the bonded wafer at the micro bubble layer as a border, wherein the base wafer is one silicon wafer selected from a group consisting of an epitaxial wafer, a nitrogen doped wafer, a hydrogen annealed wafer, a nitrogen doped and annealed wafer, and an entire N-region wafer.

9. (Previously Presented) The method of producing an SOI wafer according to Claim 7, wherein one silicon wafer selected from a group consisting of an epitaxial wafer, an FZ wafer, a nitrogen doped wafer, a hydrogen annealed wafer, an intrinsic gettering wafer, a nitrogen doped and annealed wafer, and an entire N-region wafer is used as the bond wafer.

10. (Previously Presented) The method of producing an SOI wafer according to Claim 8, wherein one silicon wafer selected from a group consisting of an epitaxial wafer, an FZ wafer, a nitrogen doped wafer, a hydrogen annealed wafer, an intrinsic gettering wafer, a nitrogen doped and annealed wafer, and an entire N-region wafer is used as the bond wafer.

11. (Previously Presented) The method of producing an SOI wafer according to Claim 8, wherein the SOI layer to be formed has a thickness of 0.3 μm or less.

12. (Previously Presented) The method of producing an SOI wafer according to Claim 10, wherein the SOI layer to be formed has a thickness of 0.3 μm or less.

13. (Previously Presented) The method of producing an SOI wafer according to Claim 7, wherein the insulator film to be formed has a thickness of 0.4 μm or less.

14. (Previously Presented) The method of producing an SOI wafer according to Claim 8, wherein the insulator film to be formed has a thickness of 0.4 μm or less.

15. (Previously Presented) The method of producing an SOI wafer according to Claim 9, wherein the insulator film to be formed has a thickness of 0.4 μm or less.

16. (Previously Presented) The method of producing an SOI wafer according to Claim 10, wherein the insulator film to be formed has a thickness of 0.4 μm or less.

17. (Previously Presented) The method of producing an SOI wafer according to Claim 11, wherein the insulator film to be formed has a thickness of 0.4 μm or less.

18. (Previously Presented) The method of producing an SOI wafer according to Claim 12, wherein the insulator film to be formed has a thickness of 0.4 μm or less.

19. (Previously Presented) An SOI wafer produced by the method according to Claim 7.

20. (Previously Presented) An SOI wafer produced by the method according to Claim 8.

21. (Previously Presented) An SOI wafer produced by the method according to Claim 9.

22. (Previously Presented) An SOI wafer produced by the method according to Claim 10.